

**Features:**

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

Typical Applications:

- AC controllers
- DC and AC motor control
- Controlled rectifiers

Part No. H100KPU-KT100dT

$I_{T(AV)}$	2000A
V_{DRM}, V_{RRM}	8000V
	8500V

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_J (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180 half sine wave 50Hz Double side cooled	$T_C=70^\circ\text{C}$	115		2000	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} $t_p=10\text{ms}$ at V_{RRM} $t_p=10\text{ms}$	115			600	mA
I_{TSM}	Surge on-state current	10ms half sine wave	115			35	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$				6125	$10^3\text{A}^2\text{s}$
V_{TO}	Threshold voltage		115			1.32	V
r_T	On-state slope resistance					0.52	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=1500\text{A}$, $F=90\text{kN}$	25			2.00	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	115			2000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$, Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$	115			200	A/μs
Q_{rr}	Recovery charge	$I_{TM}=2000\text{A}$, $t_p=4000\mu\text{s}$, $di/dt=-5\text{A}/\mu\text{s}$, $V_R=50\text{V}$	115		5000		μC
I_{GT}	Gate trigger current		25	40		300	mA
V_{GT}	Gate trigger voltage	$V_A=12\text{V}$, $I_A=1\text{A}$		0.8		3.0	V
I_H	Holding current			25		200	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	115			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Double side cooled				0.0057	C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	Clamping force 90kN				0.0015	
F_m	Mounting force			81	90	108	kN
T_{vj}	Junction temperature			-40		115	°C
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				2500		g
Outline	KT100dT						

Outline:

